

Silicon PNP Darlington Power Transistor

2SB1647

DESCRIPTION

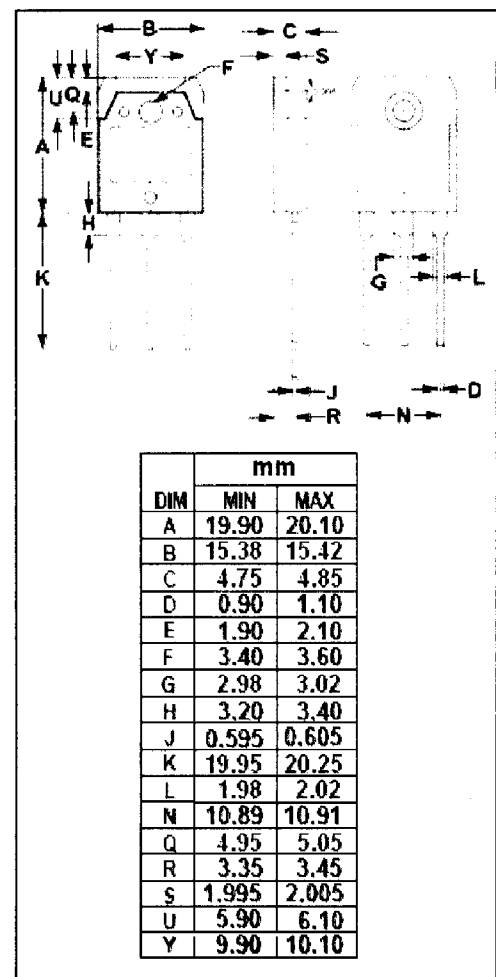
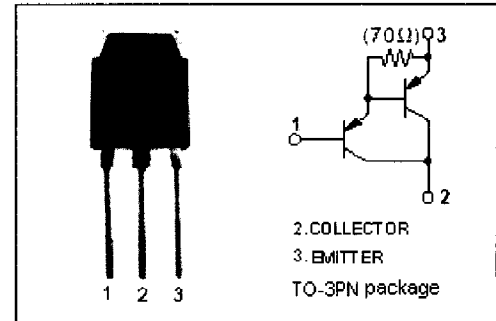
- Collector-Emitter Breakdown Voltage-
 : $V_{(BR)CEO} = -150V(\text{Min})$
- High DC Current Gain-
 : $h_{FE} = 5000(\text{Min.}) @ (I_C = -10A, V_{CE} = -4V)$
- Low Collector Saturation Voltage-
 : $V_{CE(sat)} = -2.5V(\text{Max}) @ (I_C = -10A, I_B = -10mA)$
- Complement to Type 2SD2560

APPLICATIONS

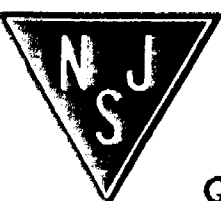
- Designed for audio, series regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	130	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA ; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -10A; I _B = -10mA			-2.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -10A; I _B = -10mA			-3.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-100	μ A
h _{FE}	DC Current Gain	I _C = -10A; V _{CE} = -4V	5000			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		320		pF
f _T	Current-Gain—Bandwidth Product	I _E = 2A ; V _{CE} = -12V		45		MHz

Switching Times

t _{on}	Turn-on Time	V _{CC} = -40V, R _L = 4 Ω, I _C = -10A; I _{B1} = -I _{B2} = -10mA,		0.7		μ s
t _{stg}	Storage Time			1.6		μ s
t _f	Fall Time			1.1		μ s

◆ h_{FE} Classifications

O	P	Y
5000-12000	6500-20000	15000-30000